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## LIST OF PUBLICATIONS and OTHER RESEARCH OUTPUTS

### Papers in Referred Journals

#### 2013

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- [3] E. Kapetanakis, A.M. Douvas, P. Argitis, P. Normand, *Radiation Sensors Based on the Generation of Mobile Protons in Organic Dielectrics*, ACS Appl. Mater. Interfaces 5 (12), 5667–5674. 2013.
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